

2SK665

Silicon N-Channel MOS FET

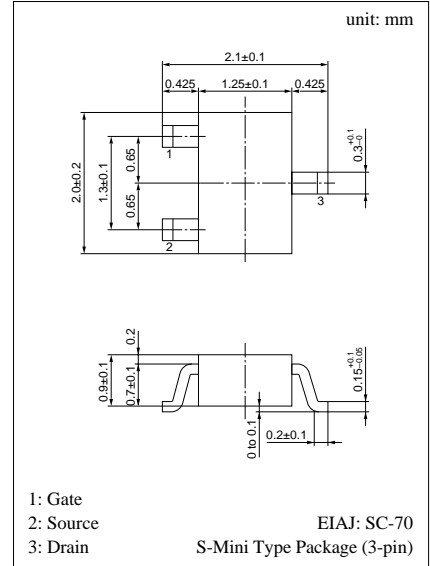
For switching

■ Features

- High-speed switching
- Small drive current owing to high input impedance
- High electrostatic breakdown voltage

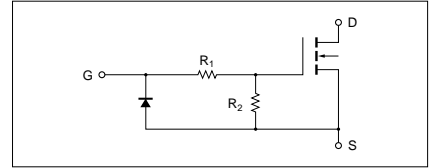
■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rated	Unit
Drain to Source voltage	V_{DS}	20	V
Gate to Source voltage	V_{GSO}	8	V
Drain current	I_D	100	mA
Max drain current	I_{DP}	200	mA
Allowable power dissipation	P_D	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C



Marking Symbol: 30

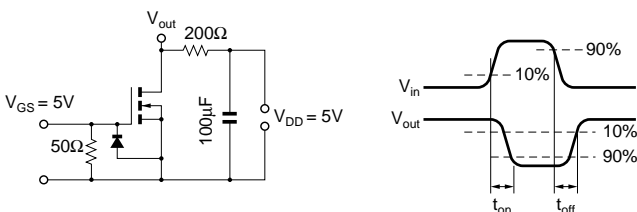
Internal Connection



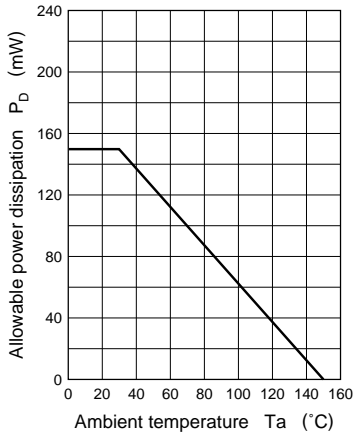
■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I_{DSS}	$V_{DS} = 10V, V_{GS} = 0$			10	μA
Gate to Source leakage current	I_{GSS}	$V_{GS} = 8V, V_{DS} = 0$	40		80	μA
Drain to Source breakdown voltage	V_{DSS}	$I_D = 100\mu A, V_{GS} = 0$	20			V
Gate threshold voltage	V_{th}	$I_D = 100\mu A, V_{DS} = V_{GS}$	1.5		3.5	V
Drain to Source ON-resistance	$R_{DS(on)}^{*3}$	$I_D = 20mA, V_{GS} = 5V$			50	Ω
Forward transfer admittance	$ Y_{fs} $	$I_D = 20mA, V_{DS} = 5V, f = 1kHz$	20			mS
High level output voltage	V_{OH}	$V_{DD} = 5V, V_{GS} = 1V, R_L = 200\Omega$	4.5			V
Low level output voltage	V_{SL}	$V_{DD} = 5V, V_{GS} = 5V, R_L = 200\Omega$			1	V
Input resistance	$R_1 + R_2^{*1}$		100		200	k Ω
Turn-on time	t_{on}^{*2}	$V_{DD} = 5V, V_{GS} = 0 \text{ to } 5V, R_L = 200\Omega$			1	μs
Turn-off time	t_{off}^{*2}	$V_{DD} = 5V, V_{GS} = 5 \text{ to } 0V, R_L = 200\Omega$			1	μs

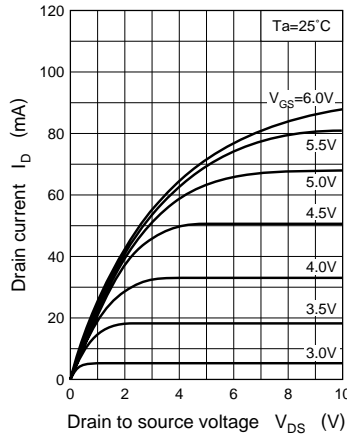
*1 Resistance ratio $R_1/R_2 = 1/50$ *2 t_{on}, t_{off} measurement circuit *3 Pulse measurement



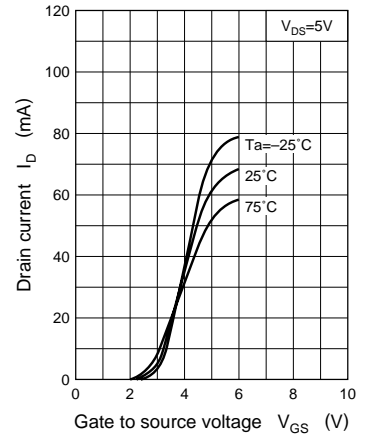
$P_D - T_a$



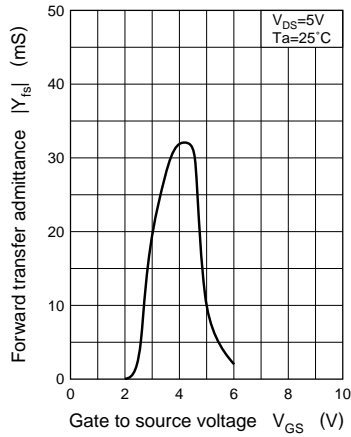
$I_D - V_{DS}$



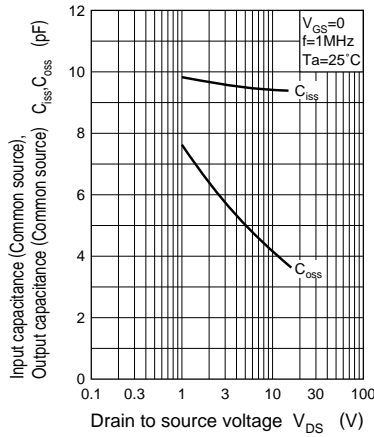
$I_D - V_{GS}$



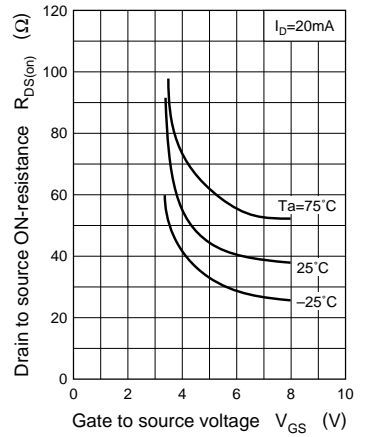
$|Y_{fs}| - V_{GS}$



$C_{iss}, C_{oss} - V_{DS}$



$R_{DS(on)} - V_{GS}$



$V_{IN} - I_O$

